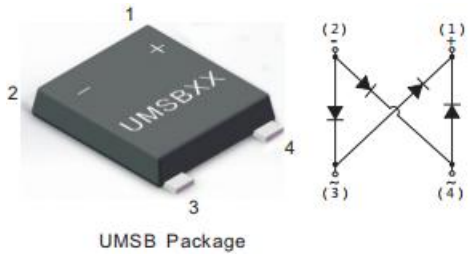
Bridge Rectifier Diode 整流桥



UMSB Package

■Features 特点

Glass passivated chip junction 玻璃钝化结
High surge current capability 高浪涌电流能力
Peak Soak Temperature 260℃ 峰值浸润温度 260 度
Package 封装: UMSB

■Maximum Rating 最大额定值

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	MSB30A	MSB30B	MSB30D	MSB30G	MSB30J	MSB30K	MSB30M	Unit 单位
Marking 印字		MB30A	MB30B	MB30D	MB30G	MB30J	MB30K	MB30M	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	3							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	100							A
Rating for Fusing 熔断值 (1ms < t < 8.3ms)	I^2t	42							A^2S
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	30							℃/W
Junction/Storage Temperature 结温和储藏温度	T_J,T_{stg}	150℃,-55to+150℃							

■Electrical Characteristics 电特性

(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F		1.1		V	I_F=3A
Reverse Current (T_A=25℃) 反向电流(T_A=125℃)	I_R			5 200	uA	V_R=V_{RRM}
Diode Capacitance 二极管电容	C_D		40		pF	V_R=4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

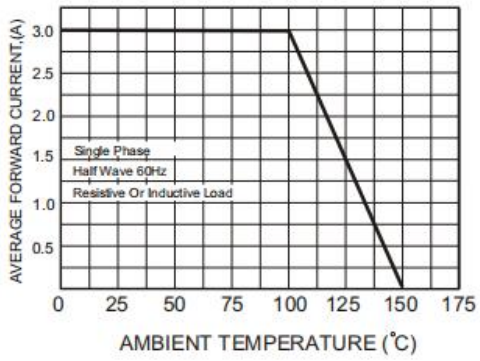


FIG.2-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

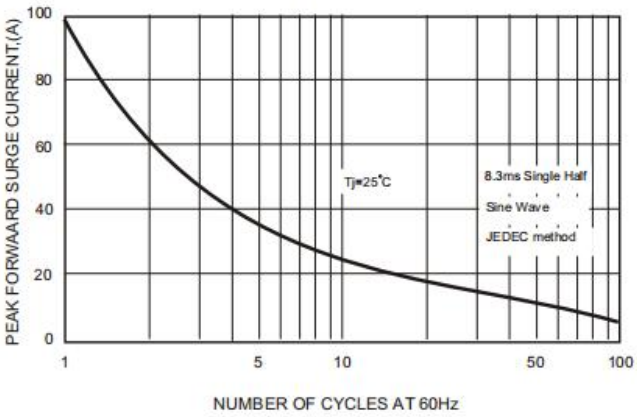


FIG.3-TYPICAL FORWARD CHARACTERISTICS

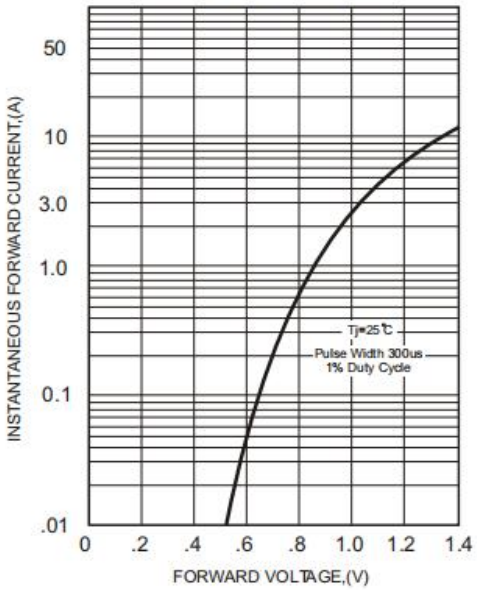
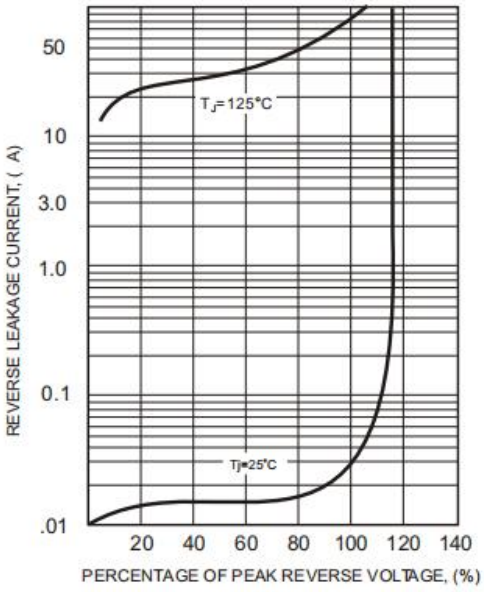
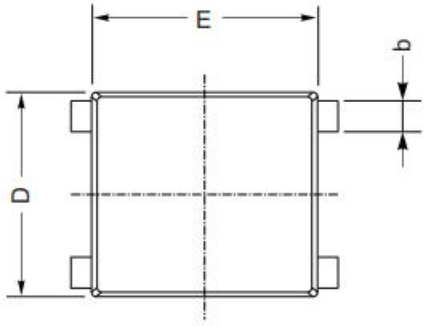
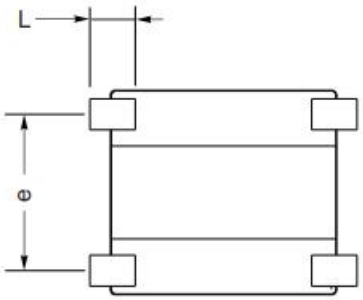


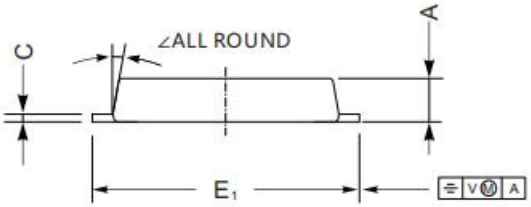
FIG.4-TYPICAL REVERSE CHARACTERISTICS



■Dimension 外形封装尺寸







UMSB mechanical data

UNIT		A	C	D	E	E_1	L	e	b	∠
mm	max	1.5	0.29	7.0	7.6	8.9	1.6	5.3	1.15	10°
	min	1.3	0.17	6.2	7.1	8.4	1.0	4.9	0.95	
mil	max	59	12	276	299	350	55	209	45	
	min	51	7	244	280	331	31.5	193	37	